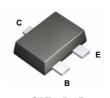


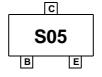
July 2007

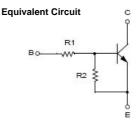
FJY3005R NPN Epitaxial Silicon Transistor

Features

- · Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R1=4.7KΩ, R2=10KΩ)
- Complement to FJY4005R







Absolute Maximum Ratings * Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current	100	mA
T _{STG}	Storage Temperature Range	-55~150	°C
T _J	Junction Temperature	150	°C
P _C	Collector Power Dissipation, by R _{θJA}	200	mW

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

Thermal Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	600	°C/W

^{*} Minimum land pad size.

Electrical Characteristics* T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Тур	MAX	Units
V _{(BR)CBO}	Collector-Emitter Breakdown Voltage	Ic = 10 uA, IE = 0	50			V
V _(BR) CEO	Collector-Base Breakdown Voltage	Ic = 100 uA, I _B = 0	50			V
Ісво	Collector-Cutoff Current	Vcb = 40 V, IE = 0			0.1	uA
hfe	DC Current Gain	Vc= 5 V, Ic = 5 mA	30			
VcE(sat)	Collector-Emitter Saturation Voltage	Ic = 10 mA, I _B = 0.5 mA			0.3	V
f⊤	Current Gain - Bandwidth Product	VcE = 10V, Ic = 5 mA		250		MHz
Ccb	Output Capacitance	Vcb = 10 V, IE = 0, f = 1.0 MHz		3.7		pF
V _I (off)	Input Off Voltage	Vce = 5 V, Ic = 100uA	0.3			V
V _I (on)	Input On Voltage	VcE = 0.3V, Ic = 20mA			2.5	V
R ₁	Input Resistor		3.2	4.7	6.2	ΚΩ
R ₁ /R ₂	Resistor Ratio		0.42	0.47	0.52	

^{*} Pulse Test: PW≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1. DC current Gain

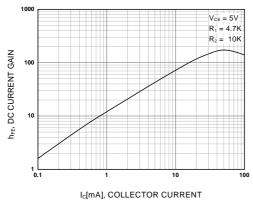


Figure 3. Input off Voltage

0.2



1.0 1.2

V, (off)[V], INPUT OFF VOLTAGE

Figure 2. Input On Voltage

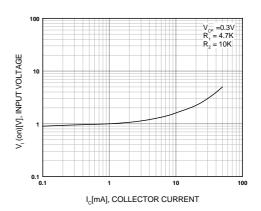
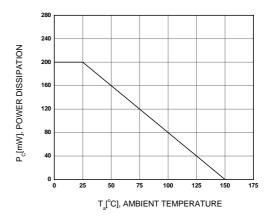


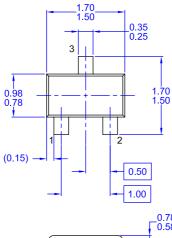
Figure 4. Power Derating

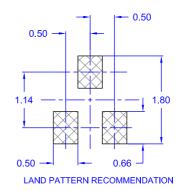


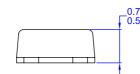
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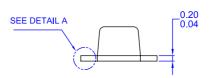
Package Dimensions

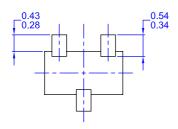
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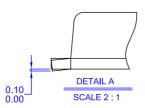












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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
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Dimensions in Millimeters



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Rev. 125